

KSB601

Low Frequency Power Amplifier Medium Speed Switching Industrial Use Complement to KSD560

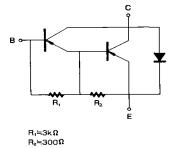


1.Base 2.Collector 3.Emitter

PNP Epitaxial Silicon Darlington Transistor

Absolute Maximum Ratings $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CBO}	Collector-Base Voltage	- 100	V	
V _{CEO}	Collector-Emitter Voltage	- 100	V	
V _{EBO}	Emitter-Base Voltage	- 7	V	
I _C	Collector Current (DC)	- 5	Α	
I _{CP}	*Collector Current (Pulse)	- 8	Α	
I _B	Base Current	- 0.5	Α	
P _C	Collector Dissipation (T _a =25°C)	1.5	W	
P _C	Collector Dissipation (T _C =25°C)	30	W	
TJ	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	- 55 ~ 150	°C	



^{*} PW≤10ms, Duty Cycle≤50%

Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{CEO} (sus)	Collector-Emitter Sustaining Voltage	I _C = - 3A, I _{B1} = - 3mA, L = 1mH	- 100			V
V _{CEX} (sus)1	Collector-Emitter Sustaining Voltage	$I_C = -3A$, $I_{B1} = -I_{B2} = -3mA$ $V_{BE}(off) = 5V$, $L = 180\mu H$ Clamped	100			V
V _{CEX} (sus)2	Collector-Emitter Sustaining Voltage	$I_C = -6A$, $I_{B1} = -12mA$ $I_{B2} = 3mA$, $V_{BE}(off) = 5V$ L = 180uH, Clamped	100			V
I _{CBO}	Collector Cut-off Current	V _{CB} = - 100V, I _E = 0			- 10	μΑ
I _{CER}	Collector Cut-off Current	$V_{CE} = -100V, R_{BE} = 51\Omega$ $T_{C} = 125^{\circ}C$			- 1	mA
I _{CEX1}	Collector Cut-off Current	$V_{CE} = -100V, V_{BE}(off) = 1.5V$			- 10	μΑ
I _{CEX2}	Collector Cut-off Current	$V_{CE} = -100V, V_{BE}(off) = 1.5V$ $T_{C} = 125^{\circ}C$			- 1	mA
I _{EBO}	Emitter Cut-off Current	V _{EB} = - 5V, I _C = 0			- 3	mA
h _{FE1} h _{FE2}	*DC Current Gain	V _{CE} = - 2V, I _C = - 3A V _{CE} = - 2V, I _C = - 5A	2000 500		15000	
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	I _C = - 3A, I _B = - 3mA			- 1.5	V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	I _C = - 3A, I _B = - 3mA			- 2	V
t _{ON}	Turn ON Time	V _{CC} = - 50V , I _C = - 3A		0.5		μs
t _S	Storage	$I_{B1} = -I_{B2} = -3mA$		1		μs
t _F	Fall time	$R_L = 17\Omega$		1		μs

^{*} Pulse Test: PW≤350μs, Duty Cycle≤2%

$\ensuremath{\mathsf{h}_{\mathsf{FE}}}$ Classification

Classification	R	0	Υ	
h _{FE1}	2000 ~ 5000	3000 ~ 7000	5000 ~ 15000	

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Typical Characteristics

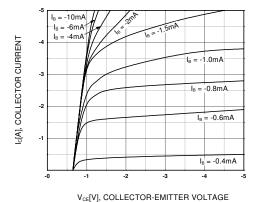


Figure 1. Static Characteristic

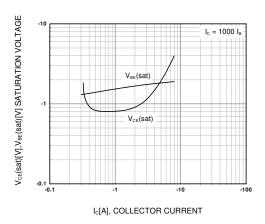


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

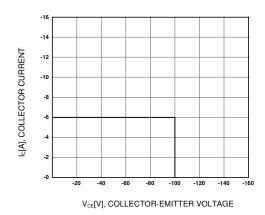


Figure 5. Reverse Bias Safe Operating Areas

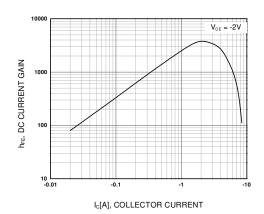


Figure 2. DC current Gain

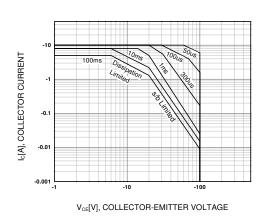


Figure 4. Safe Operating Area

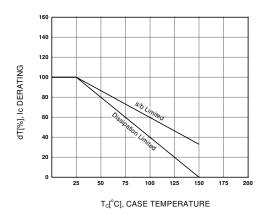


Figure 6. Derating Curve of Safe Operating Areas

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Typical Characteristics (Continued)

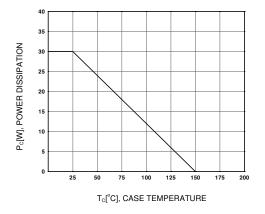
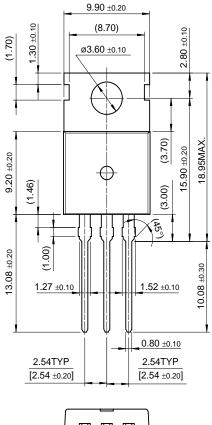


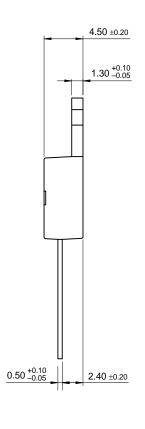
Figure 7. Power Derating

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Package Demensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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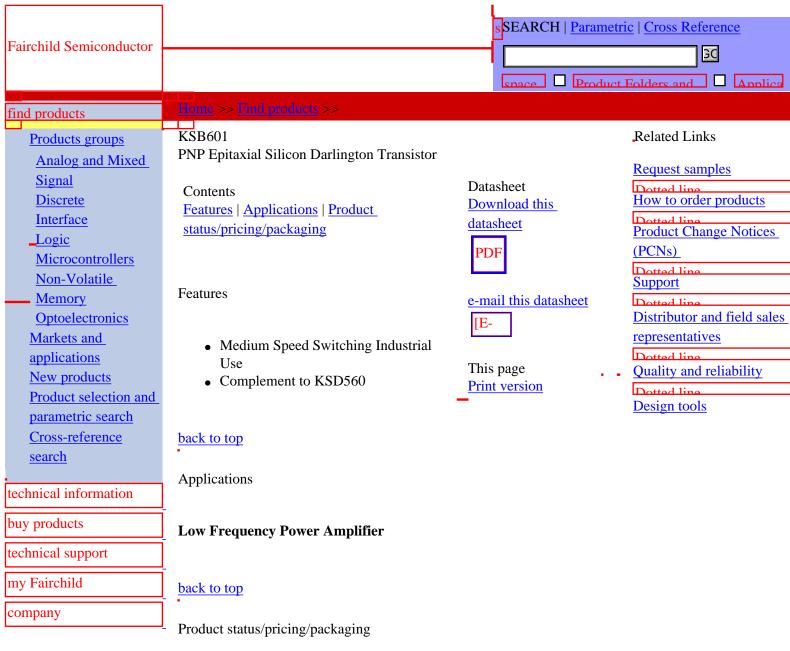
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Datasheet Identification	Product Status	Definition
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Product	Product status	Pricing*	Package type	Leads	Packing method
KSB601YTSTU	Full Production	\$0.425	TO-220	3	RAIL
KSB601Y	Full Production	\$0.425	TO-220	3	BULK
KSB601O	Full Production	\$0.425	TO-220	3	BULK
KSB601R	Full Production	\$0.425	TO-220	3	BULK
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^{* 1,000} piece Budgetary Pricing

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